Supplementary Material

Stability, electronic, and optical properties of two-dimensional

iridium trihalides with promising applications in photocatalytic

water splitting

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Contents:

Figure S1:



Figure S1 (a) Top and (b) side views of the crystal structure of the bulk phase of α -IrX₃ (X = Cl, Br, I) in the representation of the conventional cell. (c) High symmetry *k*-points of the Brillouin zone for α -IrX₃ and the path along which the band structure is evaluated.

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Figure S2:



Figure S2. The change of strain energy and the created stress in the IrX₃ monolayers under applied biaxial strain. Because a vacuum space is left along the *z* direction in the unit cell, the calculated in-plane stress components must be rescaled ^[1,2] based on the effective layer thickness d_0 of IrX₃ monolayers. We chose the lattice constant *c* of bulk IrX₃ as the d_0 , as list in Table S1, and rescale the in-plane stress components by h/d_0 , where *h* is the length of the cell along *z* axis.

Structure	a	b	с	<i>E</i> with different methods			
				DDE DDE SOC USE06 avagriment			
				FDL	FBE-SUC	HSE00	experiment
IrCl ₃	6.092	10.558	5.629	1.846	1.750	3.264	
IrCl ₃ ^[3]	5.99 ± 0.01	10.37 ± 0.02	5.99±0.01				
IrBr ₃	6.408	11.116	5.984	1.432	1.380	2.704	
IrBr ₃ * [4]	6.30	10.98	6.34				
IrI ₃	6.867	11.901	6.490	1.175	1.123	2.217	
IrI ₃ ^[5]	6.802	11.791	6.864	1.0			1.49
IrI ₃ *[11]	6.74	11.75	6.80				

Table S1. Calculated lattice constant (in Å) at PBE level, and band-gap E_g (in eV) of α -IrX₃ bulk at different levels. The asterisk (*) means the experimental results.

Figure S3:



Figure S3. Electronic structure of bulk IrX_3 obtained from HSE functional with 10% of the exact exchange.

Figure S4:



Figure S4. Electronic structure of monolayer IrX_3 obtained from (left panel) PBE and (right panel) PBE + SOC methods.





Figure S5. Electronic structure of monolayer IrX_3 obtained from (left panel) HSE06 and (right panel) HSE06 + SOC methods.





Figure S6. Electronic structure of monolayers (a) $IrCl_3$, (b) $IrBr_3$, (c) IrI_3 , and their heterojunctions (d) $IrCl_3$:IrBr₃ and (e) $IrBr_3$:IrI₃ obtained from G_0W_0 method. (f) The band structures of IrI_3 near the valence band maximum.





Figure S7. Total and projected DOS of monolayers (a) $IrCl_3$, (b) $IrBr_3$, (c) IrI_3 obtained at PBE+SOC level.





Figure S8. Top and lateral views of IrCl₃:IrBr₃ and IrBr₃:IrI₃ van der Waals heterostructures.

References

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